

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

2SK4087LS — General-Purpose Switching Device Applications

Features

- ON-resistance RDS(on)= 0.47Ω (typ.)
- Input capacitance Ciss=1200pF (typ.)
- 10V drive

Specifications

Absolute Maximum Ratings at Ta=25°C

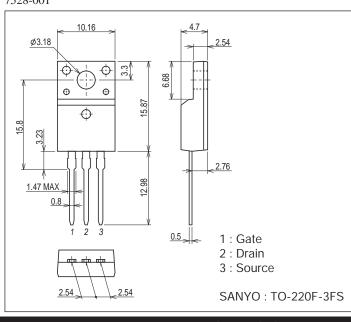
Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		600	V
Gate-to-Source Voltage	VGSS		±30	V
Drain Current (DC)	I _{Dc} *1	Limited only by maximum temperature Tch=150°C	14	А
	I _{Dpack} *2	Tc=25°C (SANYO's ideal heat dissipation condition)*3	9.2	А
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	52	А
Allowable Power Dissipation	Do		2.0	W
	PD	Tc=25°C (SANYO's ideal heat dissipation condition)*3	40	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *4	EAS		106	mJ
Avalanche Current *5	IAV		14	А

^{*1} Shows chip capability.

The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium.

Package Dimensions

unit : mm (typ) 7528-001



Product & Package Information

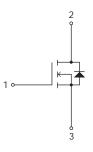
• Package : TO-220F-3FS

• JEITA, JEDEC : SC-67

• Minimum Packing Quantity: 50 pcs./magazine

Marking Electrical Connection





SANYO Semiconductor Co., Ltd.

http://semicon.sanyo.com/en/network

^{*2} Package limited.

^{*3} SANYO's condition is radiation from backside.

^{*4} V_{DD}=50V, L=1mH, I_{AV}=14A (Fig.1)

^{*5} L≤1mH, Single pulse

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Linit
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=10mA, VGS=0V	600			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =480V, V _{GS} =0V			100	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±30V, V _{DS} =0V			±100	nA
Cutoff Voltage	V _{GS} (off)	V _{DS} =10V, I _D =1mA	3		5	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =7A	4	8		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)	I _D =7A, V _G S=10V		0.47	0.61	Ω
Input Capacitance	Ciss	V _{DS} =30V, f=1MHz		1200		pF
Output Capacitance	Coss			220		pF
Reverse Transfer Capacitance	Crss			50		pF
Turn-ON Delay Time	t _d (on)	See Fig.2		27		ns
Rise Time	t _r			72		ns
Turn-OFF Delay Time	t _d (off)			144		ns
Fall Time	tf			48		ns
Total Gate Charge	Qg	V _{DS} =200V, V _{GS} =10V, I _D =14A		46		nC
Gate-to-Source Charge	Qgs			8.6		nC
Gate-to-Drain "Miller" Charge	Qgd			26.4		nC
Diode Forward Voltage	V _{SD}	I _S =14A, V _{GS} =0V		0.95	1.3	V

Fig.1 Avalanche Resistance Test Circuit

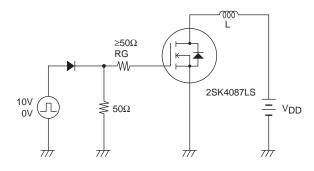
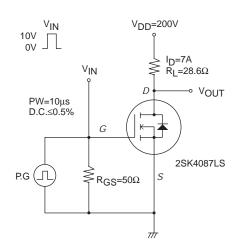
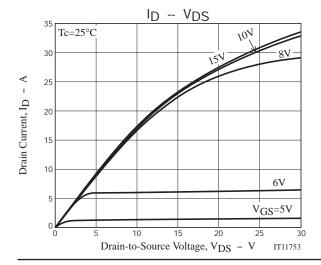
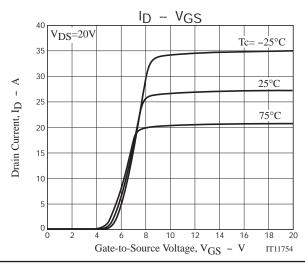
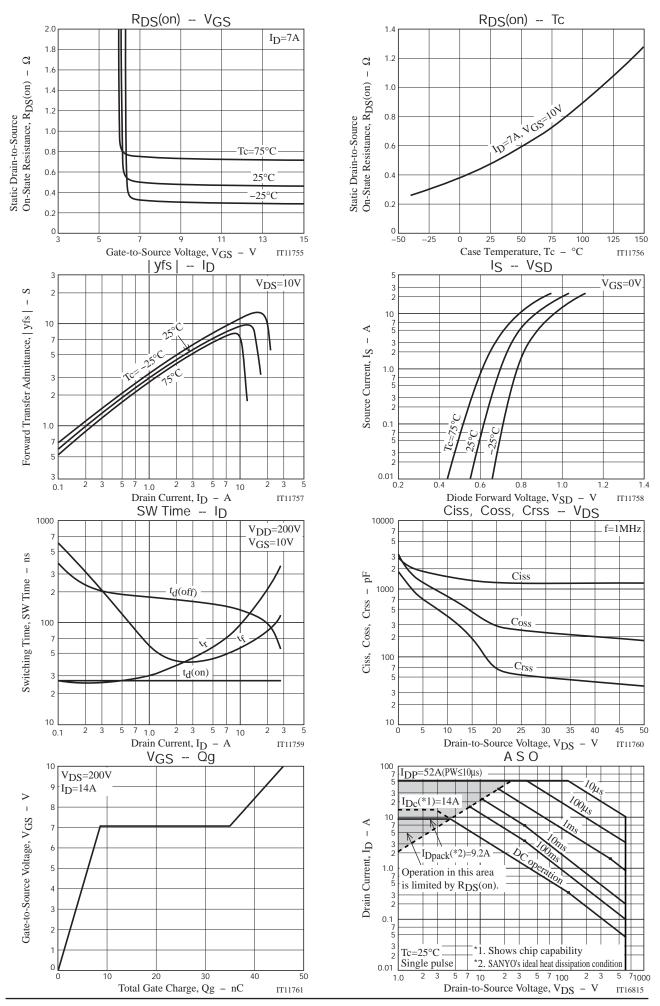


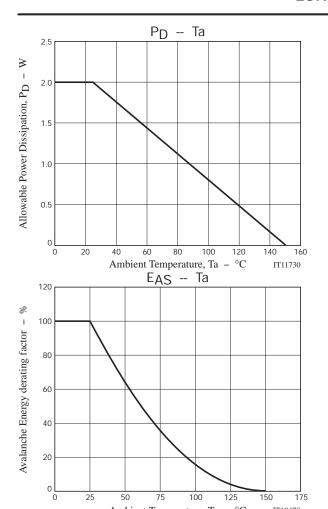
Fig.2 Switching Time Test Circuit











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Ambient Temperature, Ta - °C

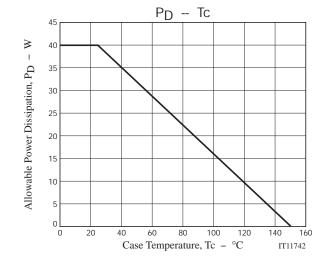
100

125

175

IT10478

150



Note on usage: Since the 2SK4087LS is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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